

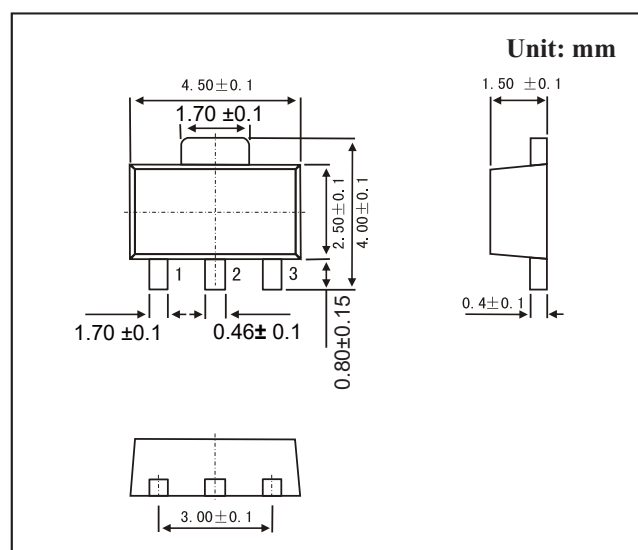
SOT-89 Plastic-Encapsulate Transistors

FEATURES

- Compliment to PXT8050
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:SOT-89 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-1.5	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	°C/W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55~150	°C

PACKAGE INFORMATION

Device	Package	Shipping
PXT8550	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -100mA$	85	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -800mA$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$		-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$		-1.2	V
Base-emitter on voltage	$V_{BE(on)}$	$I_C = -1V, V_{CE} = -10mA$		-1	V
Base-emitter positive favor voltage	V_{BEF}	$I_B = -1A$		-1.55	V
Transition frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	100		MHz
output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		20	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D	D3
Range	85-160	120-200	160-300	300-400

Marking

Marking	Y2
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■ Typical Characteristics

